

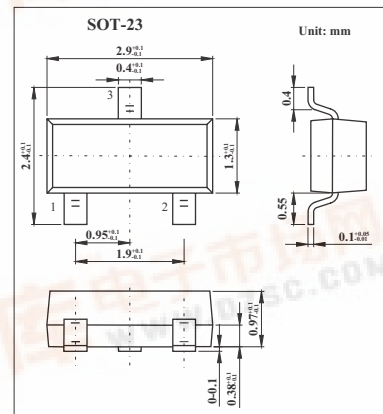
SMD Type Diodes

Silicon Epitaxial Schottky Barrier Diode

1SS345

■ Features

- Small interterminal capacitance (C=0.45pF typ).
- Low forward voltage and excellent detection efficiency(V_F=0.35V max)
- High breakdown voltage (V_R=55V).
- Very small-sized package permitting the 1SS345-applied sets to be made small and slim.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	55	V
Forward Current	I _F	10	mA
Power Dissipation	P	150	mW
Junction Temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to +125	°C
Reverse Burning	C = 25 pF Bo	2	erg

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	V _F	I _F = 1 mA			0.35	V
Forward Current	I _F	V _F = 1 V	10			mA
Reverse Voltage	V _R	I _R = 100 μA	55			V
Reverse Current	I _R	V _R = 40 V			50	μA
Interterminal Capacitance	C	V _R = 10 V, f = 1 MHz		0.45		pF

■ Marking

Marking	AH
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